74AHC273-Q100; 74AHCT273-Q100

Octal D-type flip-flop with reset; positive-edge trigger

Rev. 1 — 27 March 2013 Product data sheet

1. General description

The 74AHC273-Q100; 74AHCT273-Q100 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC273-Q100; 74AHCT273-Q100 has eight edge-triggered, D-type flip-flops with individual D inputs and Q outputs.

The common clock (CP) and master reset ($\overline{MR}$) inputs, load and reset (clear) all flip-flops simultaneously. The state of each D input, one set-up time before the LOW-to-HIGH clock transition, is transferred to the corresponding output (Qn) of the flip-flop.

All outputs are forced LOW, independent of clock or data inputs, by a LOW on the $\overline{MR}$ input.

The device is useful for applications where only the true output is required and the clock and master reset are common to all storage elements.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Ideal buffer for MOS microcontroller or memory
- Common clock and master reset
- Input levels:
  - For 74AHC273-Q100: CMOS level
  - For 74AHCT273-Q100: TTL level
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC273-Q100				
74AHC273D-Q100	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHC273PW-Q100	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74AHC273BQ-Q100	−40 °C to +125 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1
74AHCT273-Q100				
74AHCT273D-Q100	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHCT273PW-Q100	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74AHCT273BQ-Q100	−40 °C to +125 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1

4. Functional diagram

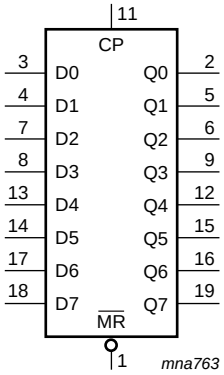


Fig 1. Logic symbol

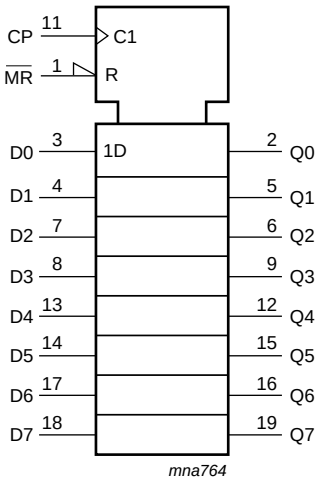


Fig 2. IEC logic symbol

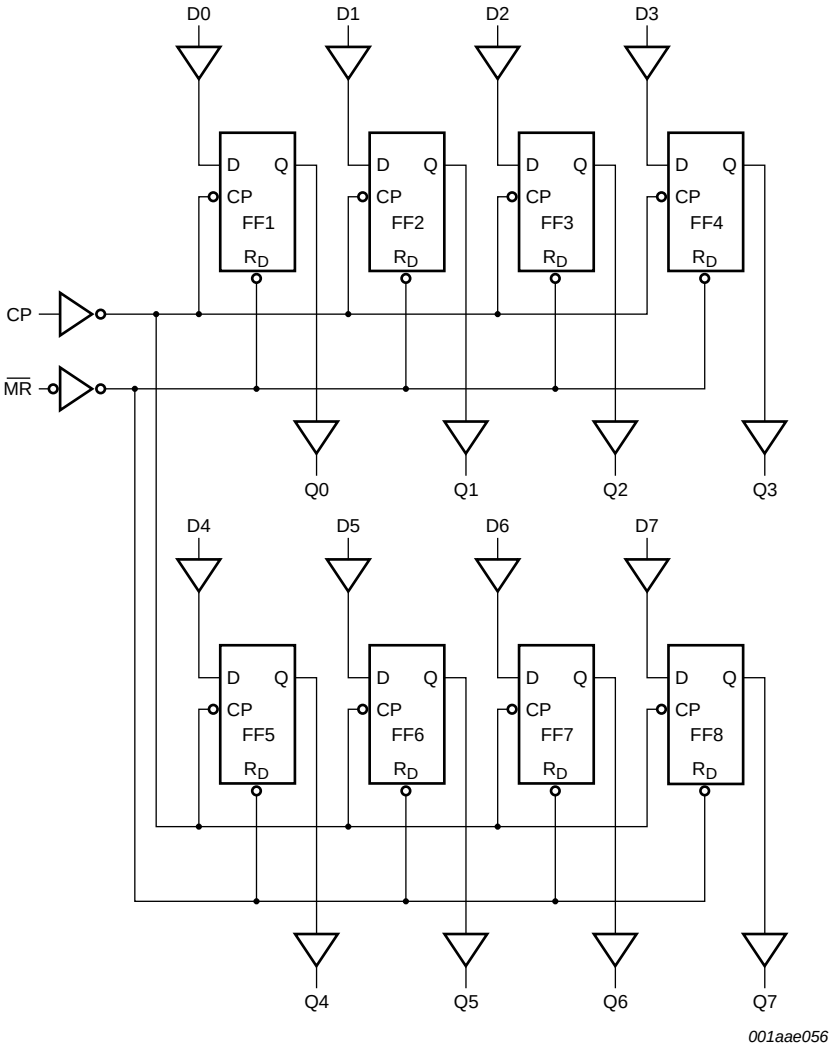


Fig 3. Logic diagram

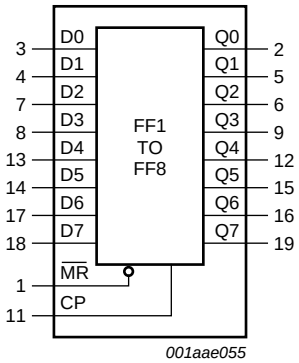


Fig 4. Functional diagram

5. Pinning information

5.1 Pinning

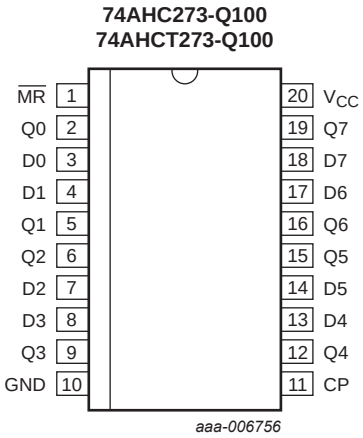
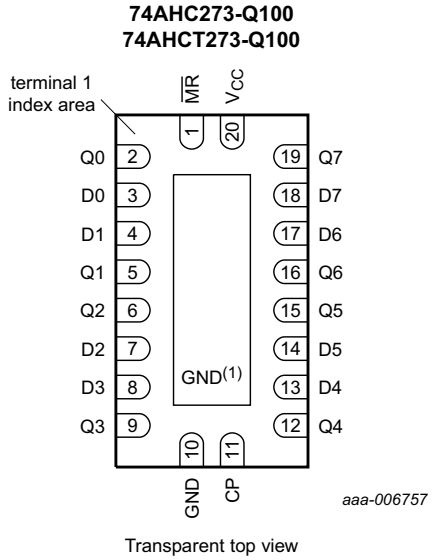


Fig 5. Pin configuration SO20 and TSSOP20



(1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to GND.

Fig 6. Pin configuration DHVQFN20

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{MR}$	1	master reset input (active LOW)
Q0, Q1, Q2, Q3, Q4, Q5, Q6, Q7	2, 5, 6, 9, 12, 15, 16, 19	flip-flop output
D0, D1, D2, D3, D4, D5, D6, D7	3, 4, 7, 8, 13, 14, 17, 18	data input
GND	10	ground (0 V)
CP	11	clock input (LOW-to-HIGH edge-triggered)
V_{CC}	20	supply voltage

6. Functional description

Table 3. Function table[1]

Operating mode	Control		Input	Output
	$\overline{MR}$	CP	Dn	Qn
Reset (clear)	L	X	X	L
Load '1'	H	↑	h	H
Load '0'	H	↑	l	L

[1] H = HIGH voltage level;
h = HIGH voltage level one set-up time prior to the LOW-to-HIGH CP transition;
L = LOW voltage level;
l = LOW voltage level one set-up time prior to the LOW-to-HIGH CP transition;
↑ = LOW-to-HIGH;
X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+7.0	V
V_I	input voltage			−0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	[1]	−20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	−20	+20	mA
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)		−25	+25	mA
I_{CC}	supply current			-	+75	mA
I_{GND}	ground current			−75	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO20 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.
For TSSOP20 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.
For DHVQFN20 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74AHC273-Q100						
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 3.0 V to 3.6 V	-	-	100	ns/V
		V_{CC} = 4.5 V to 5.5 V	-	-	20	ns/V
74AHCT273-Q100						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 4.5 V to 5.5 V	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC273-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V_{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V_{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V_{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V_{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = –50 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –50 μA; V_{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I_O = –50 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4.0 mA; V_{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I_O = –8.0 mA; V_{CC} = 4.5 V	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 50 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 μA; V_{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I_O = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V

Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	4.0	-	40	-	80	μA
C_I	input capacitance		-	3	10	-	10	-	10	pF
C_O	output capacitance		-	4	-	-	-	-	-	pF
74AHCT273-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = –50 μA	4.4	-	-	4.4	-	4.4	-	V
		I_O = –8.0 mA	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	4.0	-	40	-	80	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC}$ – 2.1 V; other pins at V_{CC} or GND; I_O = 0 A; V_{CC} = 4.5 V to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance		-	3	10	-	10	-	10	pF
C_O	output capacitance		-	4	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHC273-Q100											
t_{pd}	propagation delay	CP to Qn; see Figure 7	[2]								
		V_{CC} = 3.0 V to 3.6 V									
		C_L = 15 pF		-	6.0	13.6	1.0	16.0	1.0	17.0	ns
		C_L = 50 pF		-	8.6	17.1	1.0	19.5	1.0	21.5	ns
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		-	4.2	9	1.0	10.5	1.0	11.5	ns
		C_L = 50 pF		-	6.0	11.0	1.0	12.5	1.0	14.0	ns
		$\overline{MR}$ to Qn; see Figure 8	[3]								
		V_{CC} = 3.0 V to 3.6 V									
		C_L = 15 pF		-	5.1	13.6	1.0	16.0	1.0	17.0	ns
		C_L = 50 pF		-	7.3	17.1	1.0	19.5	1.0	21.5	ns
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		-	3.7	8.5	1.0	10.0	1.0	11.0	ns
		C_L = 50 pF		-	5.3	10.5	1.0	12.0	1.0	13.5	ns
f_{max}	maximum frequency	see Figure 7									
		V_{CC} = 3.0 V to 3.6 V									
		C_L = 15 pF		75	120	-	65	-	65	-	MHz
		C_L = 50 pF		50	75	-	45	-	45	-	MHz
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		120	165	-	100	-	100	-	MHz
		C_L = 50 pF		80	110	-	70	-	70	-	MHz
t_W	pulse width	CP HIGH or LOW; see Figure 7									
		V_{CC} = 3.0 V to 3.6 V		5.0	-	-	6.5	-	6.5	-	ns
		V_{CC} = 4.5 V to 5.5 V		5.0	-	-	5.0	-	5.0	-	ns
		$\overline{MR}$ LOW; see Figure 8									
		V_{CC} = 3.0 V to 3.6 V		5.0	-	-	6.0	-	6.0	-	ns
		V_{CC} = 4.5 V to 5.5 V		5.0	-	-	5.0	-	5.0	-	ns
t_{su}	set-up time	Dn to CP; see Figure 9									
		V_{CC} = 3.0 V to 3.6 V		3.0	-	-	3.0	-	3.0	-	ns
		V_{CC} = 4.5 V to 5.5 V		3.0	-	-	3.0	-	3.0	-	ns
t_h	hold time	Dn to CP; see Figure 9									
		V_{CC} = 3.0 V to 3.6 V		1.0	-	-	1.0	-	1.0	-	ns
		V_{CC} = 4.5 V to 5.5 V		1.0	-	-	1.0	-	1.0	-	ns

Table 7. Dynamic characteristics *…continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
t_{rec}	recovery time	$\overline{MR}$ to CP; see Figure 8									
		V_{CC} = 3.0 V to 3.6 V		2.5	-	-	2.5	-	2.5	-	ns
		V_{CC} = 4.5 V to 5.5 V		2.0	-	-	2.0	-	2.0	-	ns
C_{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC}	[4]	-	14	-	-	-	-	-	pF
74AHCT273-Q100; V_{CC} = 4.5 V to 5.5 V											
t_{pd}	propagation delay	CP to Qn; see Figure 7	[2]								
		C_L = 15 pF		-	4.0	7.5	1.0	8.8	1.0	9.5	ns
		C_L = 50 pF		-	5.8	9.2	1.0	10.5	1.0	11.5	ns
		$\overline{MR}$ to Qn; see Figure 8	[3]								
		C_L = 15 pF		-	3.9	10.0	1.0	11.6	1.0	12.5	ns
		C_L = 50 pF		-	5.6	11.0	1.0	12.6	1.0	14.0	ns
f_{max}	maximum frequency	see Figure 7									
		C_L = 15 pF		75	120	-	65	-	65	-	MHz
		C_L = 50 pF		50	75	-	45	-	45	-	MHz
t_W	pulse width	CP HIGH or LOW; see Figure 7		5.0	-	-	6.5	-	6.5	-	ns
		$\overline{MR}$ LOW; see Figure 8		5.0	-	-	6.0	-	6.0	-	ns
t_{su}	set-up time	Dn to CP; see Figure 9		3.0	-	-	3.0	-	3.0	-	ns
t_h	hold time	Dn to CP; see Figure 9		1.0	-	-	1.0	-	1.0	-	ns
t_{rec}	recovery time	$\overline{MR}$ to CP; see Figure 8		2.5	-	-	2.5	-	2.5	-	ns
C_{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC}	[4]	-	18	-	-	-	-	-	pF

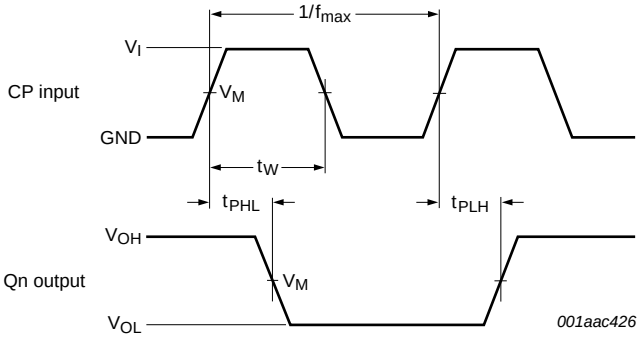
[1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] t_{pd} is the same as t_{PHL} only.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

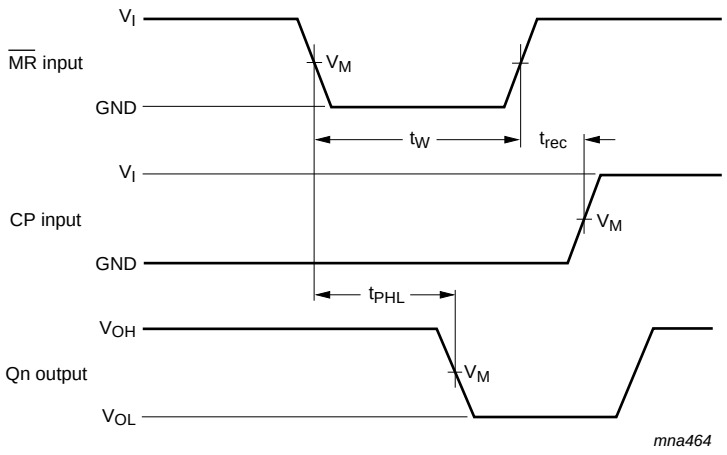
11. Waveforms



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

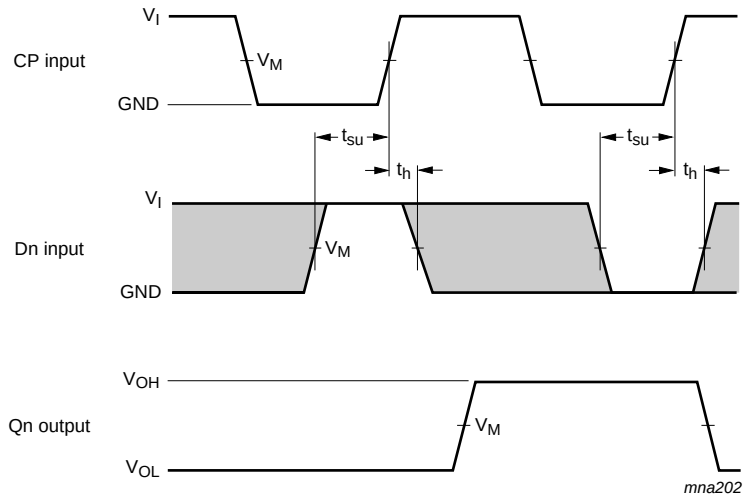
Fig 7. Clock pulse width, maximum frequency and input to output propagation delays



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 8. Master reset pulse width, recovery time and propagation delay



Measurement points are given in Table 8.

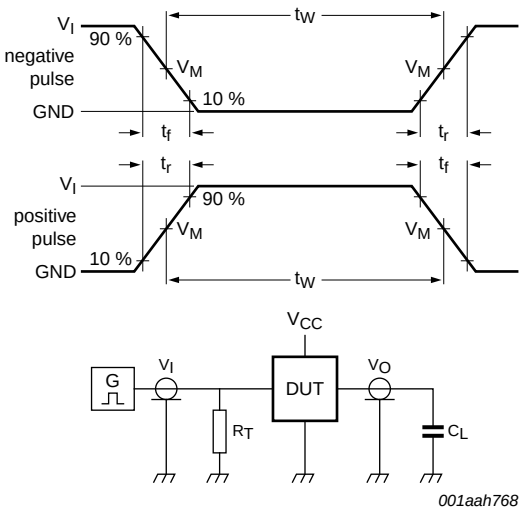
The shaded areas indicate when the input is permitted to change for predictable output performance.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 9. Data set-up and hold times

Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74AHC273-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT273-Q100	1.5 V	$0.5 \times V_{CC}$



Test data is given in Table 9.

Definitions test circuit:

R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = load capacitance including jig and probe capacitance.

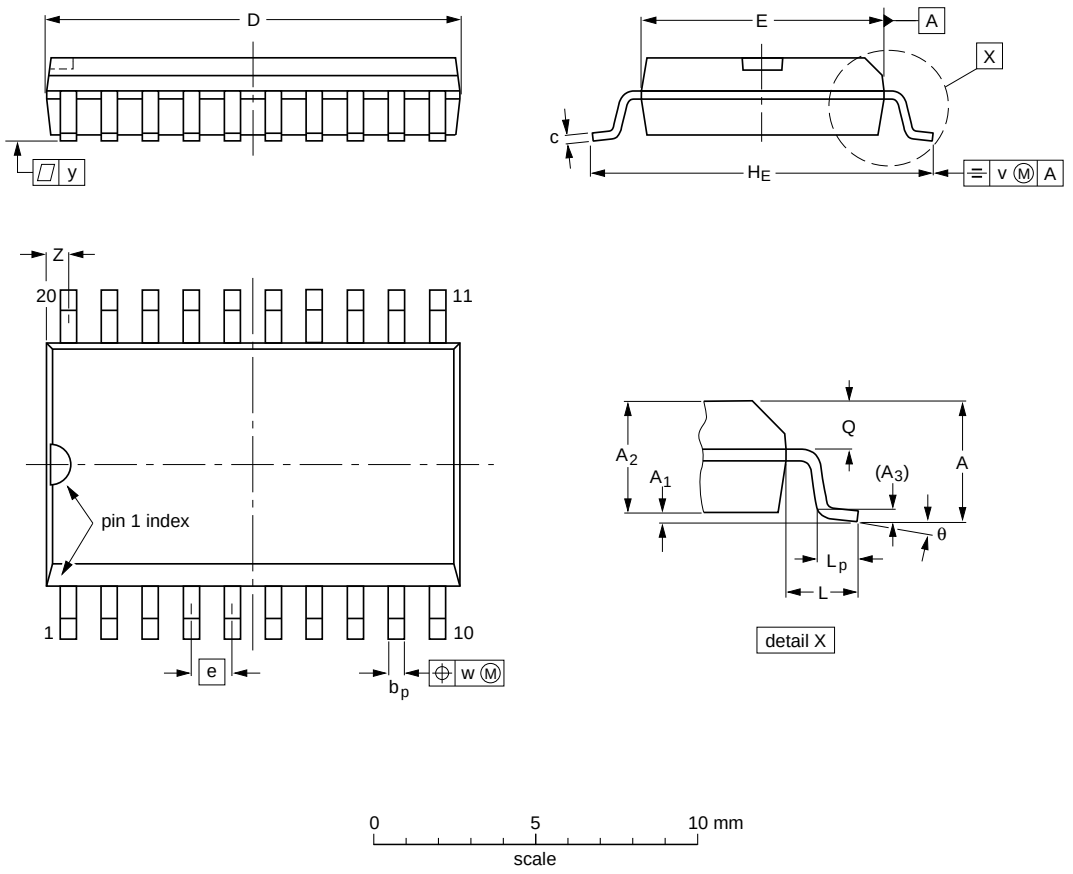
Fig 10. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
74AHC273-Q100	V_{CC}	≤ 3.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}
74AHCT273-Q100	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm **SOT163-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8^o 0^o
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

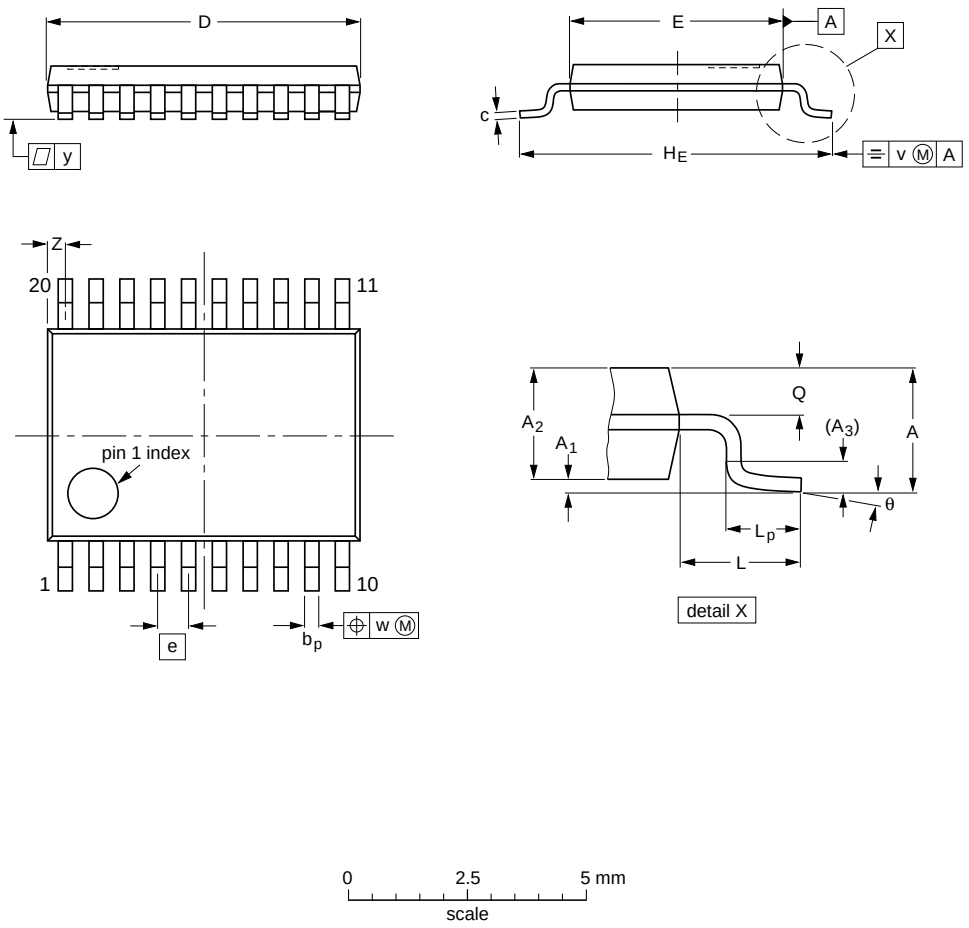
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT163-1	075E04	MS-013				~~99-12-27~~ 03-02-19

Fig 11. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm **SOT360-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8^o 0^o

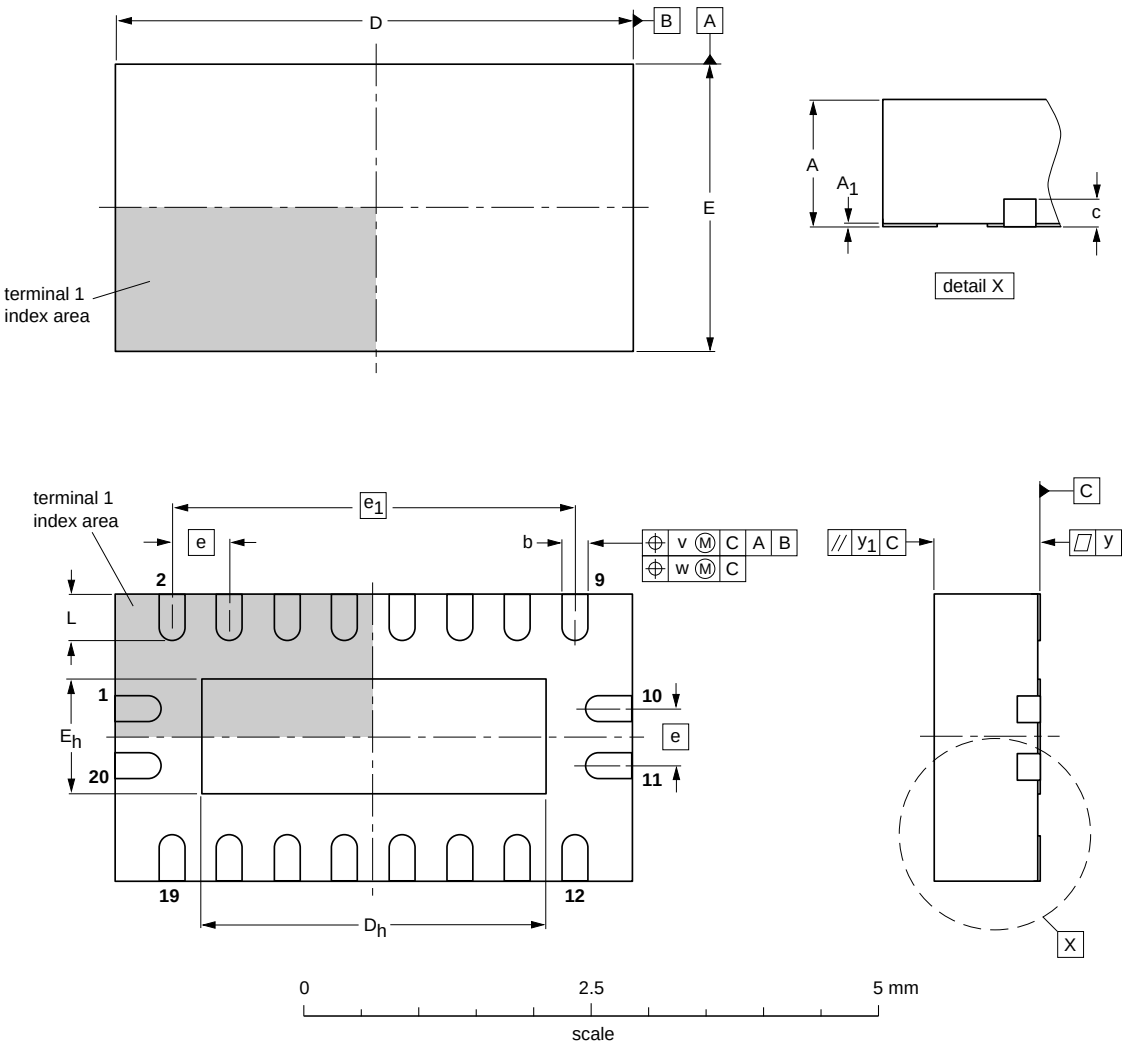
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT360-1		MO-153				~~99-12-27~~ 03-02-19

Fig 12. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm **SOT764-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	4.6 4.4	3.15 2.85	2.6 2.4	1.15 0.85	0.5	3.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT764-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 13. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
MIL	Military
MOS	Metal-Oxide Semiconductor

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT273_Q100 v.1	20130327	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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